



24NM65

Power MOSFET

24A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

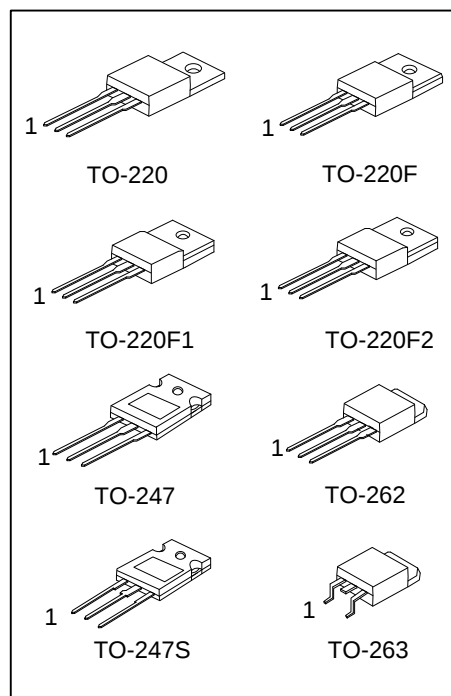
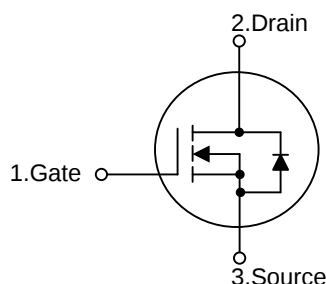
DESCRIPTION

The **UTC 24NM65** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} \leq 0.16 \Omega$ @ $V_{GS}=10V$, $I_D=12A$
- * High Switching Speed
- * 100% Avalanche Tested

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
24NM65L-TA3-T	24NM65G-TA3-T	TO-220	G	D	S	Tube
24NM65L-TF1-T	24NM65G-TF1-T	TO-220F1	G	D	S	Tube
24NM65L-TF2-T	24NM65G-TF2-T	TO-220F2	G	D	S	Tube
24NM65L-TF3-T	24NM65G-TF3-T	TO-220F	G	D	S	Tube
24NM65L-T47-T	24NM65G-T47-T	TO-247	G	D	S	Tube
24NM65L-T47S-T	24NM65G-T47S-T	TO-247S	G	D	S	Tube
24NM65L-T2Q-T	24NM65G-T2Q-T	TO-262	G	D	S	Tube
24NM65L-TQ2-T	24NM65G-TQ2-T	TO-263	G	D	S	Tube
24NM65L-TQ2-R	24NM65G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

24NM65G-TA3-T (1) Packing Type (2) Package Type (3) Green Package		(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, T47: TO-247, T47S: TO-247S, T2Q: TO-262, TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_{D}	24	A
	Pulsed (Note 2)	I_{DM}	96	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	725	mJ
Peak Diode Recovery dv/dt		dv/dt	10.5	V/ns
Power Dissipation	TO-220/TO-262 TO-263	P_{D}	150	W
	TO-220F/TO-220F1 TO-220F2		32	W
	TO-247/TO-247S		170	W
Junction Temperature		T_{J}	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 58\text{mH}$, $I_{\text{AS}} = 5.0\text{A}$, $V_{\text{DD}} = 50\text{V}$, $R_{\text{G}} = 25\Omega$, Starting $T_{\text{J}} = 25^{\circ}\text{C}$

4. $I_{\text{SD}} \leq 24\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{\text{DD}} \leq BV_{\text{DSS}}$, Starting $T_{\text{J}} = 25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-262/TO-263	θ_{JA}	62.5	$^{\circ}\text{C/W}$
	TO-247/TO-247S		40	
Junction to Case	TO-220/TO-262 TO-263	θ_{JC}	0.83	$^{\circ}\text{C/W}$
	TO-220F/TO-220F1 TO-220F2		3.9	
	TO-247/TO-247S		0.74	

■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^\circ\text{C}$, unless otherwise specified)

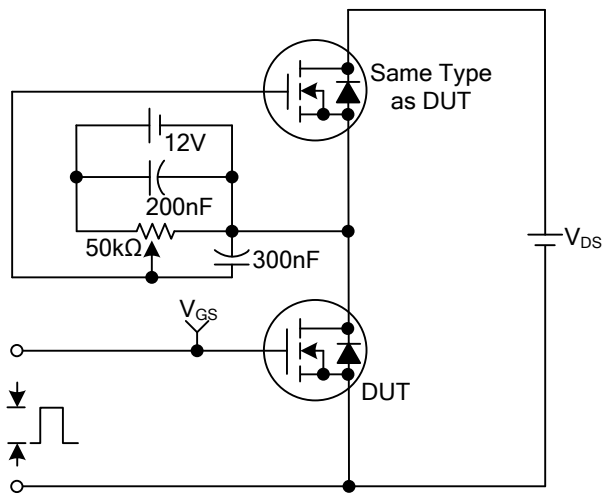
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	650			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =650V, V _{GS} =0V			50	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =12A			0.16	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		1980		pF
Output Capacitance		C _{OSS}			1200		pF
Reverse Transfer Capacitance		C _{RSS}			100		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =520V, V _{GS} =10V, I _D =24A I _G =1mA (Note1, 2)		66		nC
Gate to Source Charge		Q _{GS}			10		nC
Gate to Drain Charge		Q _{GD}			22		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DS} =100V, V _{GS} =10V, I _D =24A, R _G =25Ω (Note1, 2)		28		ns
Rise Time		t _R			36		ns
Turn-OFF Delay Time		t _{D(OFF)}			240		ns
Fall-Time		t _F			120		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				24	A
Maximum Body-Diode Pulsed Current		I _{SM}				96	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =24A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	I _S =24A, V _{GS} =0V,		640		ns
Body Diode Reverse Recovery Charge		Q _{rr}	dI _F /dt=100A/μs		13		μC

Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

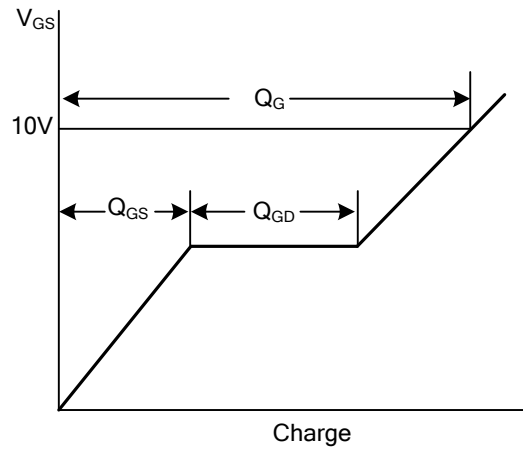
2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

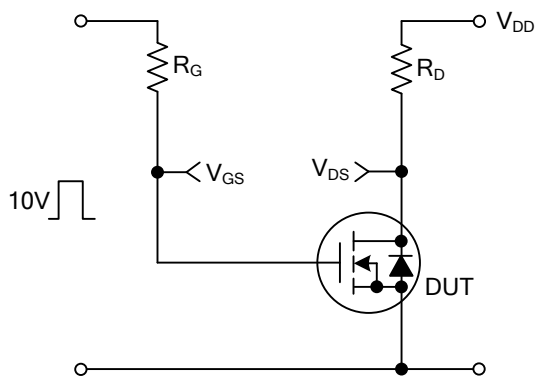
Gate Charge Test Circuit



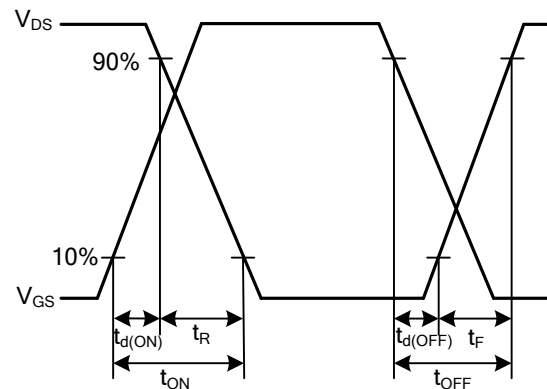
Gate Charge Waveforms



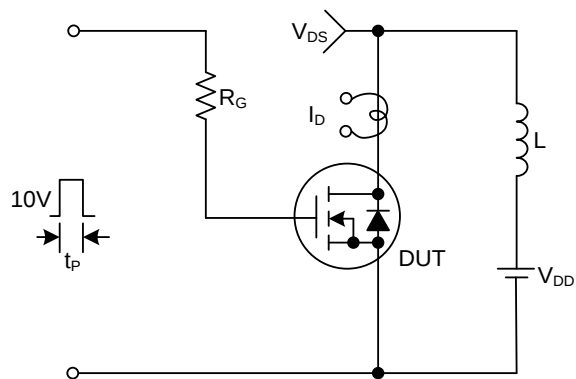
Resistive Switching Test Circuit



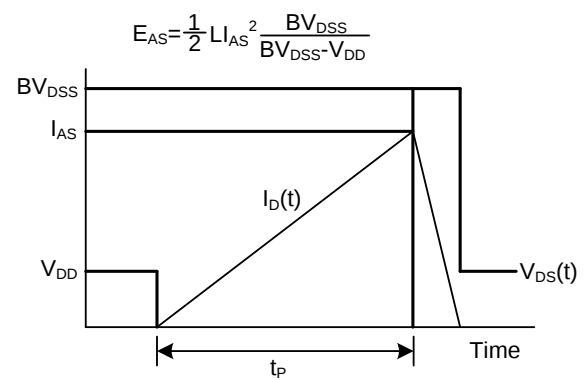
Resistive Switching Waveforms



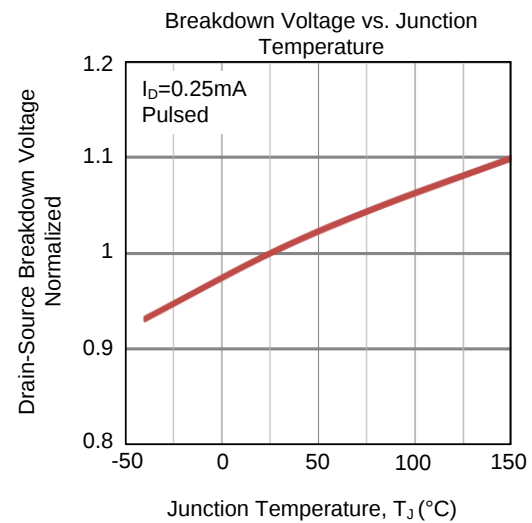
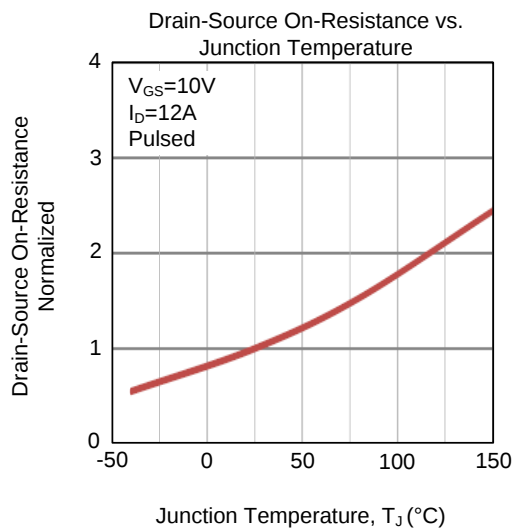
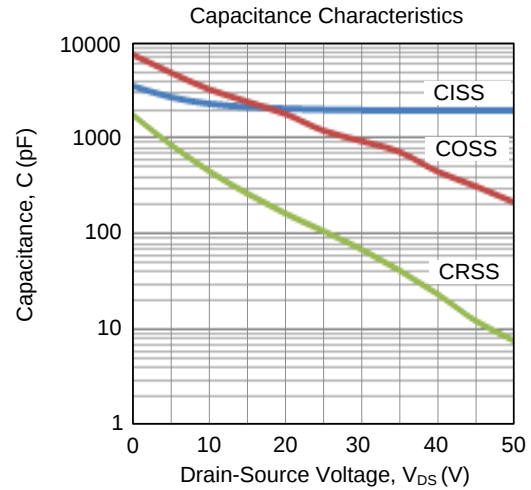
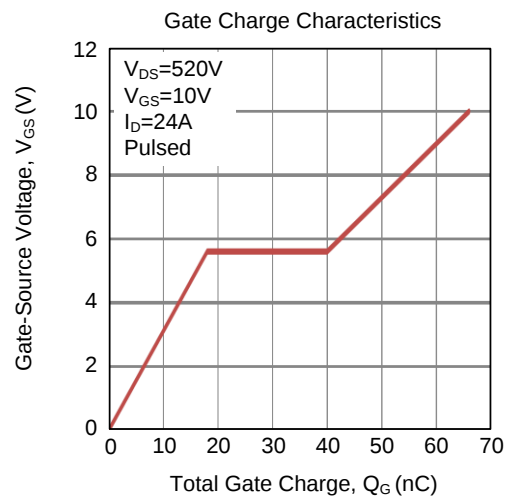
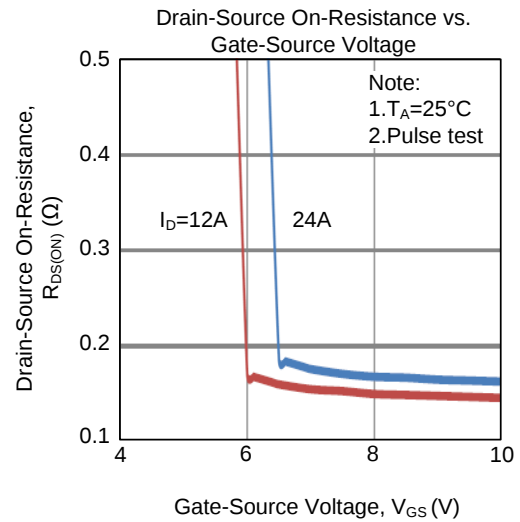
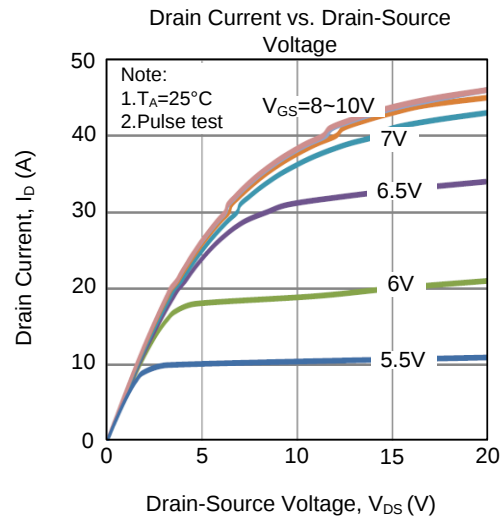
Unclamped Inductive Switching Test Circuit



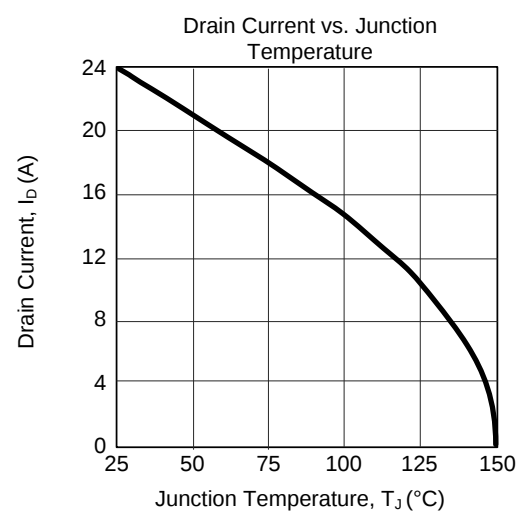
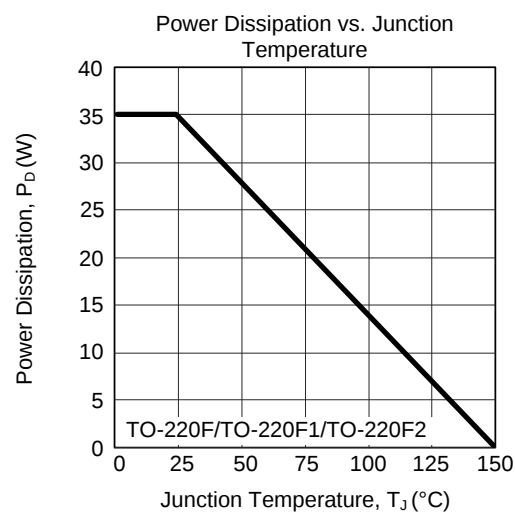
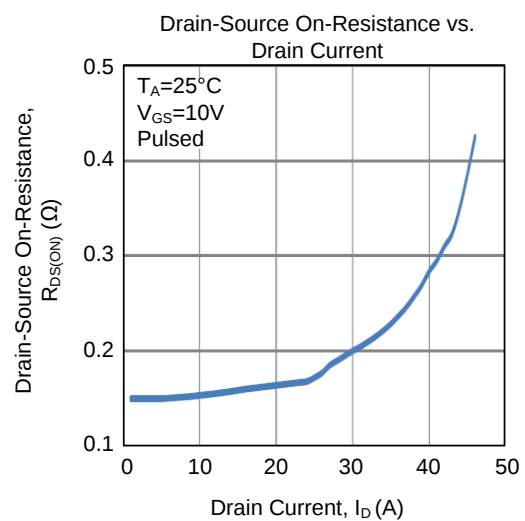
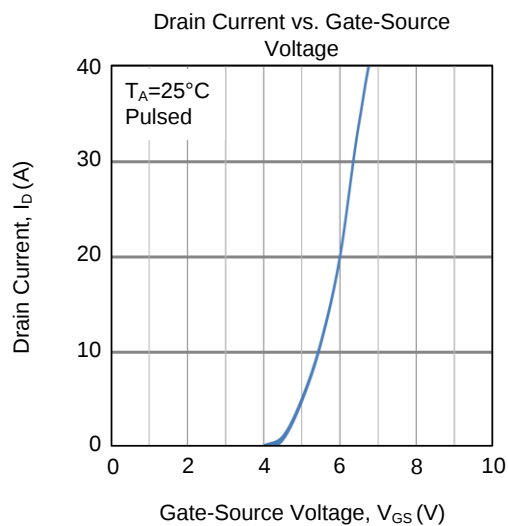
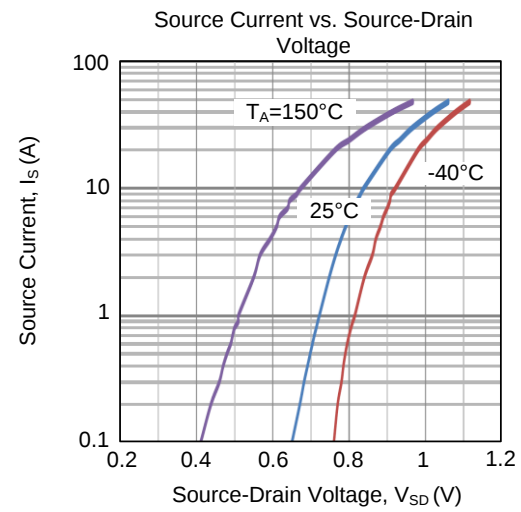
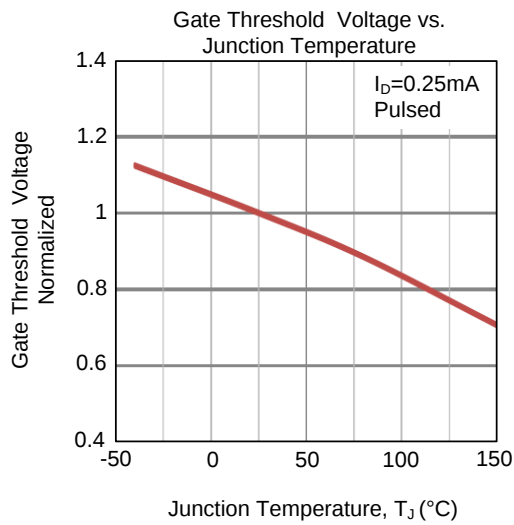
Unclamped Inductive Switching Waveforms



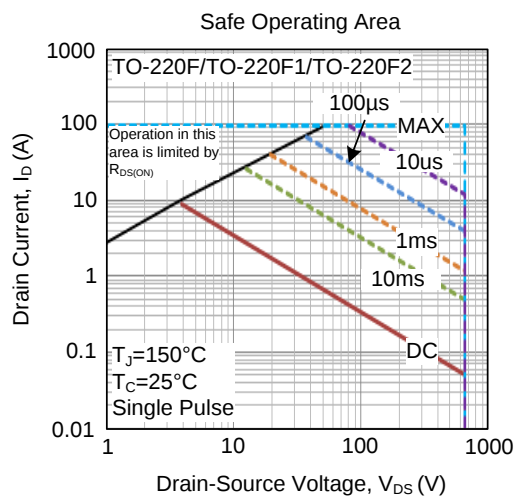
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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